

## 2SK1316-VB Datasheet

### N-Channel 650V (D-S) Super Junction Power MOSFET

| PRODUCT SUMMARY                    |                        |     |
|------------------------------------|------------------------|-----|
| $V_{DS}$ (V) at $T_J$ max.         | 650                    |     |
| $R_{DS(on)}$ at 25 °C ( $\Omega$ ) | $V_{GS} = 10\text{ V}$ | 0.7 |
| $Q_g$ max. (nC)                    | 25                     |     |
| $Q_{gs}$ (nC)                      | 2.0                    |     |
| $Q_{gd}$ (nC)                      | 2.7                    |     |
| Configuration                      | Single                 |     |

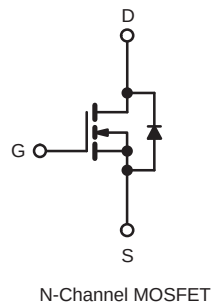
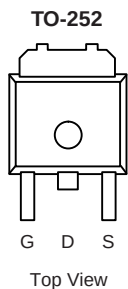
#### FEATURES

- Low figure-of-merit (FOM)  $R_{on} \times Q_g$
- Low input capacitance ( $C_{iss}$ )
- Reduced switching and conduction losses
- Ultra low gate charge ( $Q_g$ )
- Avalanche energy rated (UIS)



#### APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
  - High-intensity discharge (HID)
  - Fluorescent ballast lighting
- Industrial



| ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted) |                         |                         |                                   |              |      |
|---------------------------------------------------------------------------|-------------------------|-------------------------|-----------------------------------|--------------|------|
| PARAMETER                                                                 |                         |                         | SYMBOL                            | LIMIT        | UNIT |
| Drain-Source Voltage                                                      |                         |                         | V <sub>DS</sub>                   | 650          | V    |
| Gate-Source Voltage                                                       |                         |                         | V <sub>GS</sub>                   | ± 30         |      |
| Continuous Drain Current (T <sub>J</sub> = 150 °C)                        | V <sub>GS</sub> at 10 V | T <sub>C</sub> = 25 °C  | I <sub>D</sub>                    | 7            | A    |
|                                                                           |                         | T <sub>C</sub> = 100 °C |                                   | 6            |      |
| Pulsed Drain Current <sup>a</sup>                                         |                         |                         | I <sub>DM</sub>                   | 10           |      |
| Linear Derating Factor                                                    |                         |                         |                                   | 1.67/1.5/0.3 | W/°C |
| Single Pulse Avalanche Energy <sup>b</sup>                                |                         |                         | E <sub>AS</sub>                   | 86           | mJ   |
| Maximum Power Dissipation                                                 |                         |                         | P <sub>D</sub>                    | 83/83/31     | W    |
| Operating Junction and Storage Temperature Range                          |                         |                         | T <sub>J</sub> , T <sub>stg</sub> | -55 to +150  | °C   |
| Drain-Source Voltage Slope                                                | T <sub>J</sub> = 125 °C |                         | dV/dt                             | 50           | V/ns |
| Reverse Diode dV/dt <sup>d</sup>                                          |                         |                         |                                   | 4.5          |      |
| Soldering Recommendations (Peak Temperature) <sup>c</sup>                 | for 10 s                |                         |                                   | 300          | °C   |

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50\text{ V}$ , starting  $T_J = 25\text{ }^{\circ}\text{C}$ ,  $L = 28.2\text{ mH}$ ,  $R_g = 25\text{ }\Omega$ ,  $I_{AS} = 3.5\text{ A}$ .
- 1.6 mm from case.
- $I_{SD} \leq I_D$ ,  $dI/dt = 100\text{ A}/\mu\text{s}$ , starting  $T_J = 25\text{ }^{\circ}\text{C}$ .

**THERMAL RESISTANCE RATINGS**

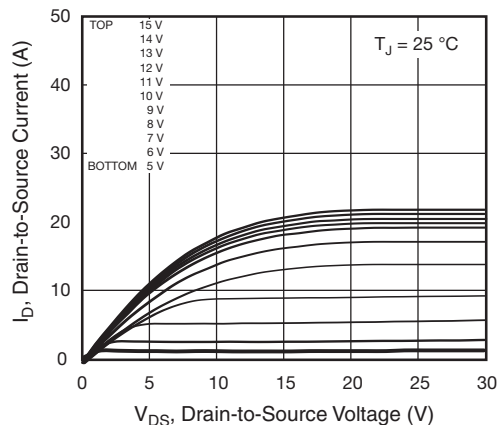
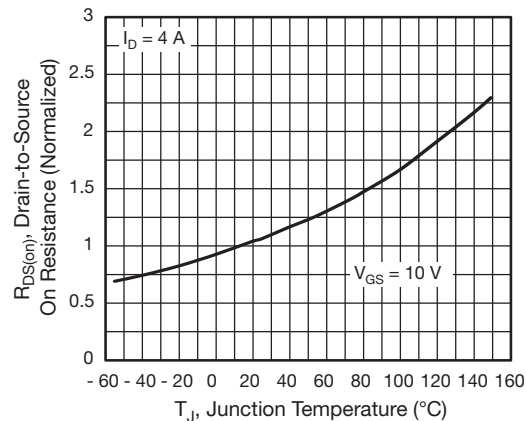
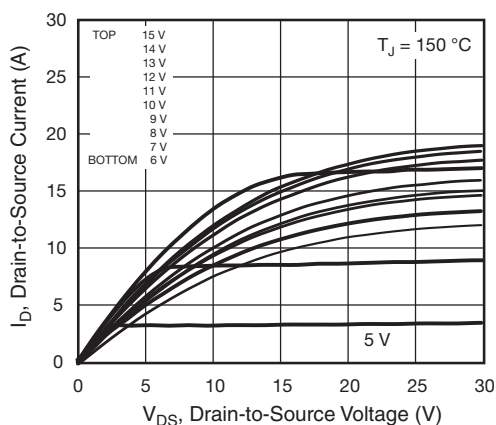
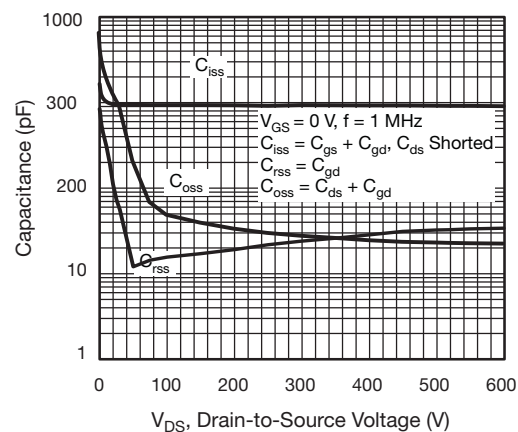
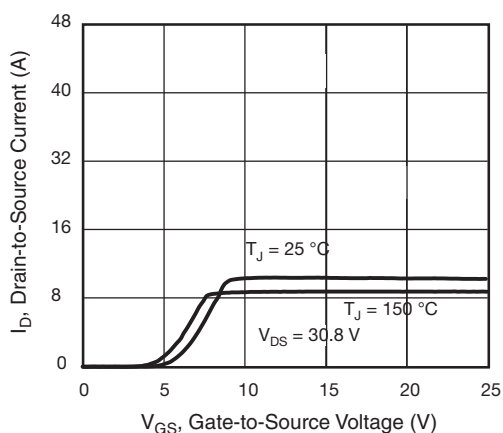
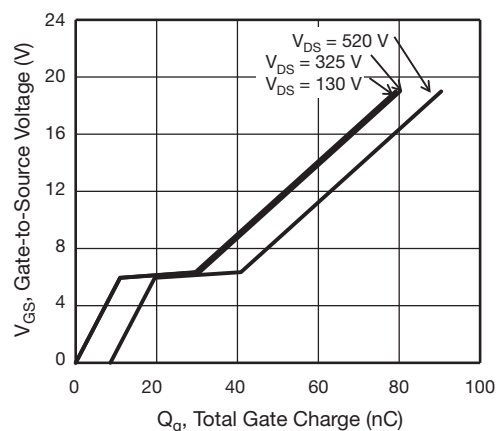
| PARAMETER                        | SYMBOL     | TYP. | MAX. | UNIT |
|----------------------------------|------------|------|------|------|
| Maximum Junction-to-Ambient      | $R_{thJA}$ | -    | 63   | °C/W |
| Maximum Junction-to-Case (Drain) | $R_{thJC}$ | -    | 0.6  |      |

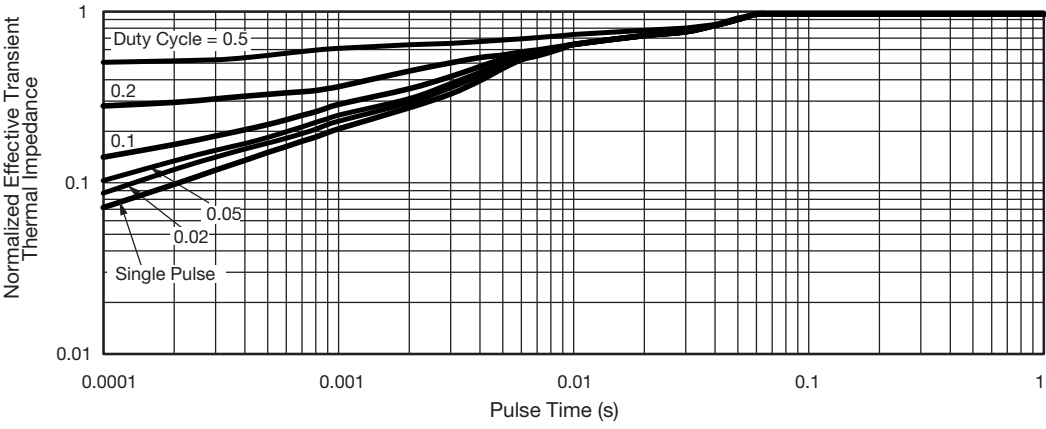
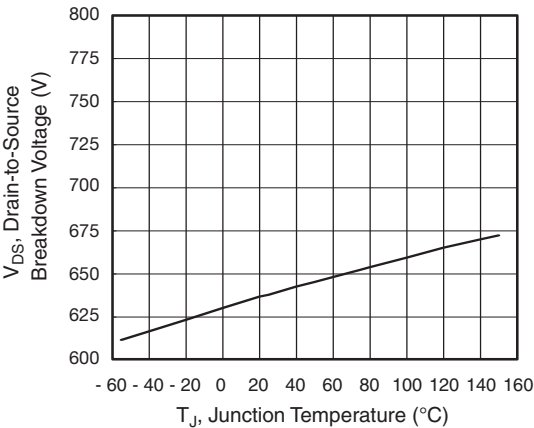
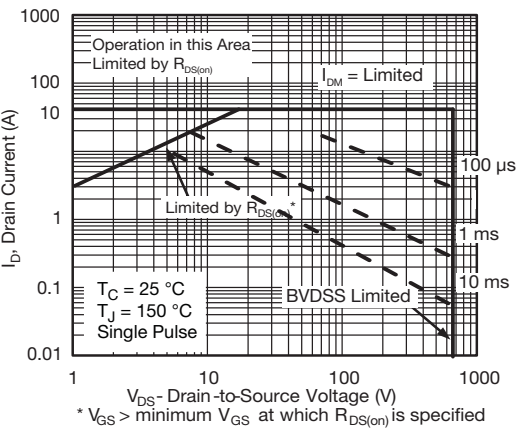
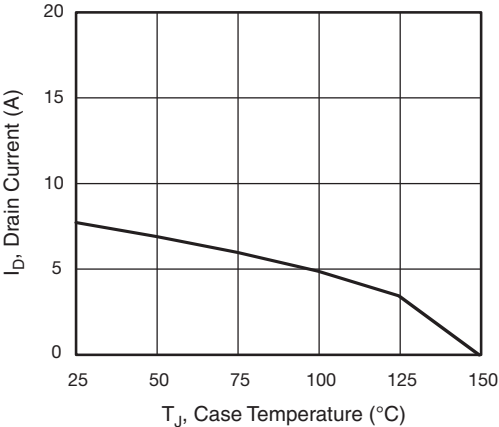
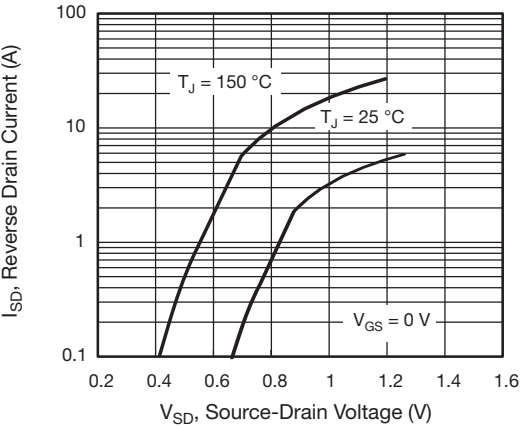
**SPECIFICATIONS** ( $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

| PARAMETER                                                 | SYMBOL                           | TEST CONDITIONS                                                                                                                                         |                                               | MIN. | TYP. | MAX.  | UNIT |
|-----------------------------------------------------------|----------------------------------|---------------------------------------------------------------------------------------------------------------------------------------------------------|-----------------------------------------------|------|------|-------|------|
| Static                                                    |                                  |                                                                                                                                                         |                                               |      |      |       |      |
| Drain-Source Breakdown Voltage                            | V <sub>DS</sub>                  | V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA                                                                                                          |                                               | 650  | -    | -     | V    |
| V <sub>DS</sub> Temperature Coefficient                   | ΔV <sub>DS</sub> /T <sub>J</sub> | Reference to 25 °C, I <sub>D</sub> = 1 mA                                                                                                               |                                               | -    | 0.65 | -     | V/°C |
| Gate-Source Threshold Voltage (N)                         | V <sub>GS(th)</sub>              | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA                                                                                             |                                               | 2    | -    | 4     | V    |
| Gate-Source Leakage                                       | I <sub>GSS</sub>                 | V <sub>GS</sub> = ± 20 V                                                                                                                                |                                               | -    | -    | ± 100 | nA   |
|                                                           |                                  | V <sub>GS</sub> = ± 30 V                                                                                                                                |                                               | -    | -    | ± 1   | μA   |
| Zero Gate Voltage Drain Current                           | I <sub>DSS</sub>                 | V <sub>DS</sub> = 650 V, V <sub>GS</sub> = 0 V                                                                                                          |                                               | -    | -    | 1     | μA   |
|                                                           |                                  | V <sub>DS</sub> = 520 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C                                                                                 |                                               | -    | -    | 10    |      |
| Drain-Source On-State Resistance                          | R <sub>DS(on)</sub>              | V <sub>GS</sub> = 10 V                                                                                                                                  | I <sub>D</sub> = 4 A                          | -    | 0.70 | -     | Ω    |
| Forward Transconductance                                  | g <sub>fs</sub>                  | V <sub>DS</sub> = 30 V, I <sub>D</sub> = 4 A                                                                                                            |                                               | -    | 16   | -     | S    |
| Dynamic                                                   |                                  |                                                                                                                                                         |                                               |      |      |       |      |
| Input Capacitance                                         | C <sub>iss</sub>                 | V <sub>GS</sub> = 0 V,<br>V <sub>DS</sub> = 100 V,<br>f = 1 MHz                                                                                         |                                               | -    | 360  | -     | pF   |
| Output Capacitance                                        | C <sub>oss</sub>                 |                                                                                                                                                         |                                               | -    | 25   | -     |      |
| Reverse Transfer Capacitance                              | C <sub>rss</sub>                 |                                                                                                                                                         |                                               | -    | 12   | -     |      |
| Effective Output Capacitance, Energy Related <sup>a</sup> | C <sub>o(er)</sub>               | V <sub>DS</sub> = 0 V to 520 V, V <sub>GS</sub> = 0 V                                                                                                   |                                               | -    | 45   | -     | pF   |
| Effective Output Capacitance, Time Related <sup>b</sup>   | C <sub>o(tr)</sub>               |                                                                                                                                                         |                                               | -    | 62   | -     |      |
| Total Gate Charge                                         | Q <sub>g</sub>                   | V <sub>GS</sub> = 10 V                                                                                                                                  | I <sub>D</sub> = 4 A, V <sub>DS</sub> = 520 V | -    | 25   | -     | nC   |
| Gate-Source Charge                                        | Q <sub>gs</sub>                  |                                                                                                                                                         |                                               | -    | 2.0  | -     |      |
| Gate-Drain Charge                                         | Q <sub>gd</sub>                  |                                                                                                                                                         |                                               | -    | 2.7  | -     |      |
| Turn-On Delay Time                                        | t <sub>d(on)</sub>               | V <sub>DD</sub> = 520 V, I <sub>D</sub> = 4 A,<br>V <sub>GS</sub> = 10 V, R <sub>g</sub> = 9.1 Ω                                                        |                                               | -    | 25   | -     | ns   |
| Rise Time                                                 | t <sub>r</sub>                   |                                                                                                                                                         |                                               | -    | 55   | -     |      |
| Turn-Off Delay Time                                       | t <sub>d(off)</sub>              |                                                                                                                                                         |                                               | -    | 70   | -     |      |
| Fall Time                                                 | t <sub>f</sub>                   |                                                                                                                                                         |                                               | -    | 40   | -     |      |
| Gate Input Resistance                                     | R <sub>g</sub>                   | f = 1 MHz, open drain                                                                                                                                   |                                               | -    | 3.5  | -     | Ω    |
| Drain-Source Body Diode Characteristics                   |                                  |                                                                                                                                                         |                                               |      |      |       |      |
| Continuous Source-Drain Diode Current                     | I <sub>S</sub>                   | MOSFET symbol showing the integral reverse p - n junction diode<br> |                                               | -    | -    | 7     | A    |
| Pulsed Diode Forward Current                              | I <sub>SM</sub>                  |                                                                                                                                                         |                                               | -    | -    | 18    |      |
| Diode Forward Voltage                                     | V <sub>SD</sub>                  | T <sub>J</sub> = 25 °C, I <sub>S</sub> = 4 A, V <sub>GS</sub> = 0 V                                                                                     |                                               | -    | -    | 1.5   | V    |
| Reverse Recovery Time                                     | t <sub>rr</sub>                  | T <sub>J</sub> = 25 °C, I <sub>F</sub> = I <sub>S</sub> = 4 A,<br>dI/dt = 100 A/μs, V <sub>R</sub> = 400 V                                              |                                               | -    | 190  | -     | ns   |
| Reverse Recovery Charge                                   | Q <sub>rr</sub>                  |                                                                                                                                                         |                                               | -    | 2.3  | -     | μC   |
| Reverse Recovery Current                                  | I <sub>RRM</sub>                 |                                                                                                                                                         |                                               | -    | 10   | -     | A    |

**Notes**

- a.  $C_{oss(er)}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .  
 b.  $C_{oss(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Fig. 1 - Typical Output Characteristics**

**Fig. 4 - Normalized On-Resistance vs. Temperature**

**Fig. 2 - Typical Output Characteristics**

**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**

**Fig. 3 - Typical Transfer Characteristics**

**Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage**



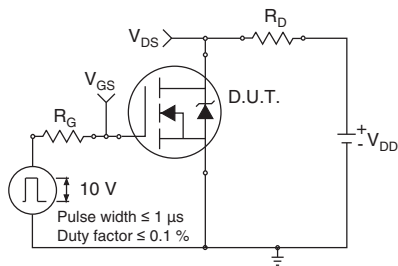


Fig. 12 - Switching Time Test Circuit

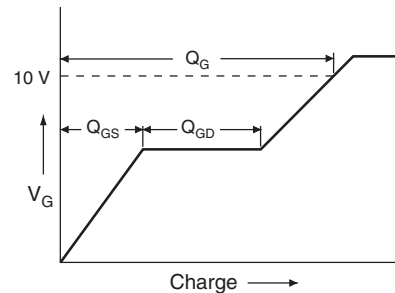


Fig. 16 - Basic Gate Charge Waveform

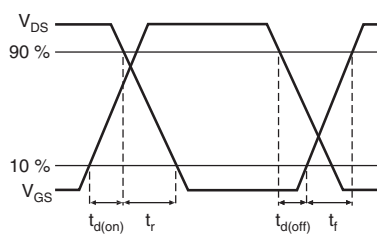


Fig. 13 - Switching Time Waveforms

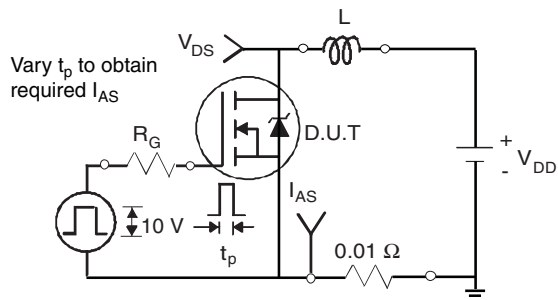


Fig. 14 - Unclamped Inductive Test Circuit

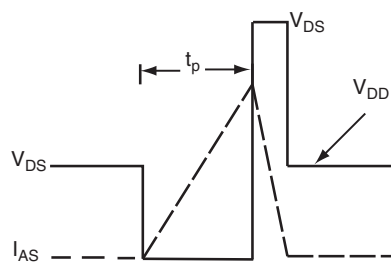


Fig. 15 - Unclamped Inductive Waveforms

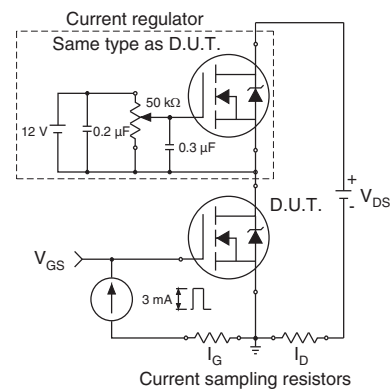
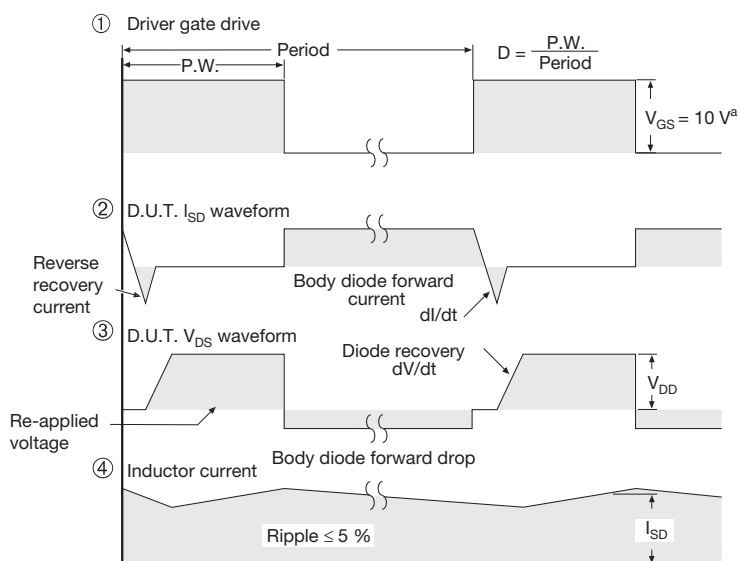
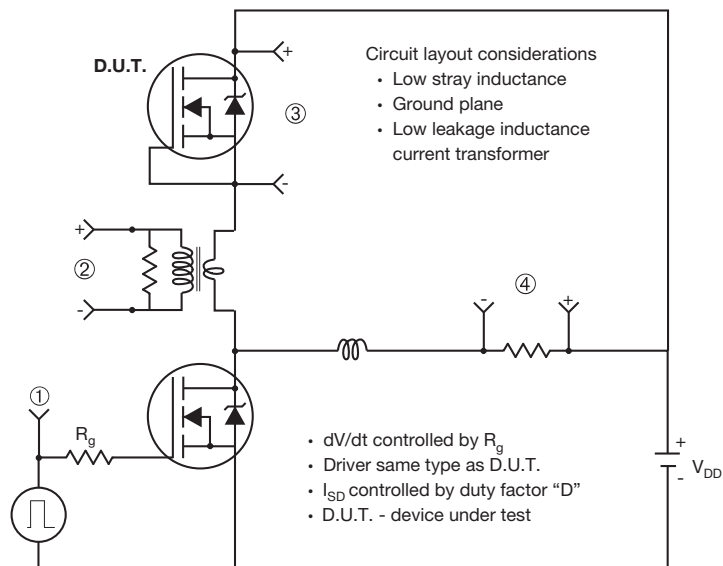


Fig. 17 - Gate Charge Test Circuit

### Peak Diode Recovery $dV/dt$ Test Circuit

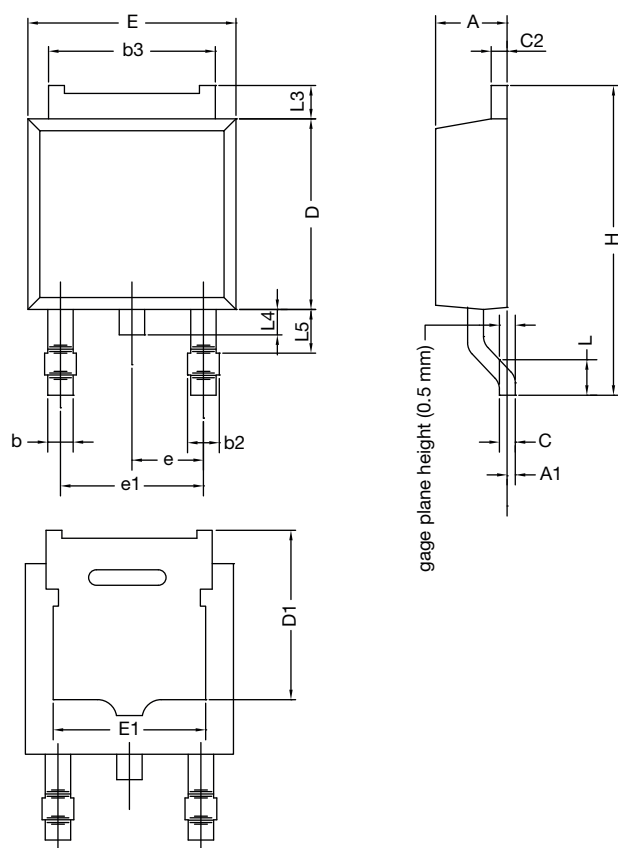


#### Note

a.  $V_{GS} = 5 V$  for logic level devices

**Fig. 18 - For N-Channel**

## TO-252AA CASE OUTLINE



| DIM.                            | MILLIMETERS |       | INCHES    |       |
|---------------------------------|-------------|-------|-----------|-------|
|                                 | MIN.        | MAX.  | MIN.      | MAX.  |
| A                               | 2.18        | 2.38  | 0.086     | 0.094 |
| A1                              | -           | 0.127 | -         | 0.005 |
| b                               | 0.64        | 0.88  | 0.025     | 0.035 |
| b2                              | 0.76        | 1.14  | 0.030     | 0.045 |
| b3                              | 4.95        | 5.46  | 0.195     | 0.215 |
| C                               | 0.46        | 0.61  | 0.018     | 0.024 |
| C2                              | 0.46        | 0.89  | 0.018     | 0.035 |
| D                               | 5.97        | 6.22  | 0.235     | 0.245 |
| D1                              | 5.21        | -     | 0.205     | -     |
| E                               | 6.35        | 6.73  | 0.250     | 0.265 |
| E1                              | 4.32        | -     | 0.170     | -     |
| H                               | 9.40        | 10.41 | 0.370     | 0.410 |
| e                               | 2.28 BSC    |       | 0.090 BSC |       |
| e1                              | 4.56 BSC    |       | 0.180 BSC |       |
| L                               | 1.40        | 1.78  | 0.055     | 0.070 |
| L3                              | 0.89        | 1.27  | 0.035     | 0.050 |
| L4                              | -           | 1.02  | -         | 0.040 |
| L5                              | 1.14        | 1.52  | 0.045     | 0.060 |
| ECN: X12-0247-Rev. M, 24-Dec-12 |             |       |           |       |
| DWG: 5347                       |             |       |           |       |

### Note

- Dimension L3 is for reference only.

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